

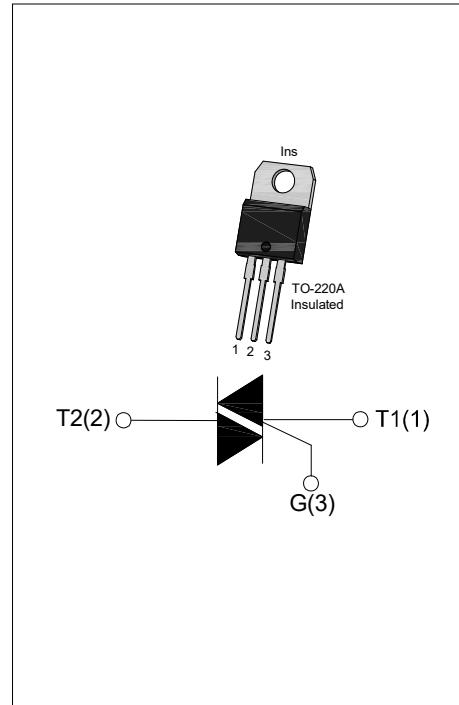


JST06A-600BW 6A TRIACs

Rev.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JST06A-600BW triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, the products especially recommended for use on inductive load. From all three terminals to external heatsink, JST06A -600BW provides a rated insulation voltage of 2500 V_{RMS}, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant. (2011/65/EU)



MAIN FEATURES

Symbol	Value	Unit
I _{T(RMS)}	6	A
V _{DRM} / V _{RMM}	600	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T _{stg}	-40 – 150	°C
Operating junction temperature range		T _j	-40 – 125	°C
Repetitive peak off-state voltage (T _j =25°C)		V _{DRM}	600	V
Repetitive peak reverse voltage (T _j =25°C)		V _{RMM}	600	V
RMS on-state current TO-220A(Ins) (T _c =100°C)		I _{T(RMS)}	6	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I _{TSM}	60	A
I ² t value for fusing (tp=10ms)		I ² t	18	A ² s
Critical rate of rise of on-state current (I _G =2×I _{GT})	I - II - III IV	dl/dt	50 10	A/μs
Peak gate current		I _{GM}	2	A
Average gate power dissipation		P _{G(AV)}	1	W
Peak gate power		P _{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D = 12V$ $R_L = 30\Omega$	I - II - III	MAX	50	mA
V_{GT}		I - II - III	MAX	1.5	V
V_{GD}	$V_D = V_{DRM}$ $T_j = 125^\circ\text{C}$ $R_L = 3.3K\Omega$	I - II - III	MIN	0.2	V
I_L	$I_G = 1.2I_{GT}$	I - III	MAX	70	mA
		II		80	
I_H	$I_{TM} = 0.2A$		MAX	60	mA
dv/dt	$V_D = 2/3V_{DRM}$ Gate Open $T_j = 125^\circ\text{C}$		MIN	1000	V/ μ s
(dI/dt)c	Without sunbber $T_j = 125^\circ\text{C}$		MIN	5.3	A/ms

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM} = 8.5A$	$t_p = 380\mu\text{s}$	$T_j = 25^\circ\text{C}$	1.5
V_{TO}	Threshold voltage		$T_j = 125^\circ\text{C}$	0.93
R_d	Dynamic resistance		$T_j = 125^\circ\text{C}$	$m\Omega$
I_{DRM}	$V_D = V_{DRM}$	$V_R = V_{RRM}$	$T_j = 25^\circ\text{C}$	5
I_{RRM}			$T_j = 125^\circ\text{C}$	1

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)	2.9	$^\circ\text{C}/\text{W}$

ORDERING INFORMATION

<u>J</u>	<u>ST</u>	<u>06</u>	<u>A</u>	<u>-600</u>	<u>BW</u>	<u>-/</u>
<u>JieJie Microelectronics Co.,Ltd</u>						
	<u>Triacs</u>					<u>Blank: Tube</u>
		<u>$I_{T(RMS)}:6A$</u>				
			<u>A:TO-220A(Ins)</u>			
				<u>600: $V_{DRM} / V_{RRM} \geq 600V$</u>		<u>BW: $I_{GT1-3} \leq 50mA$</u>

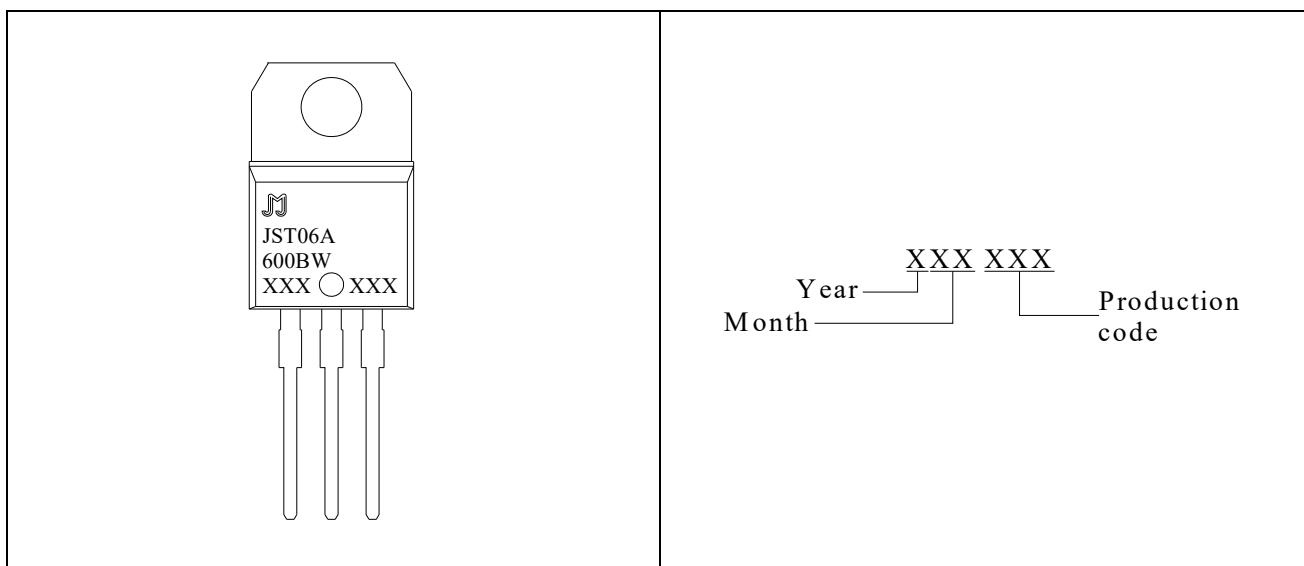
MARKING

FIG.1: Maximum power dissipation versus RMS on-state current

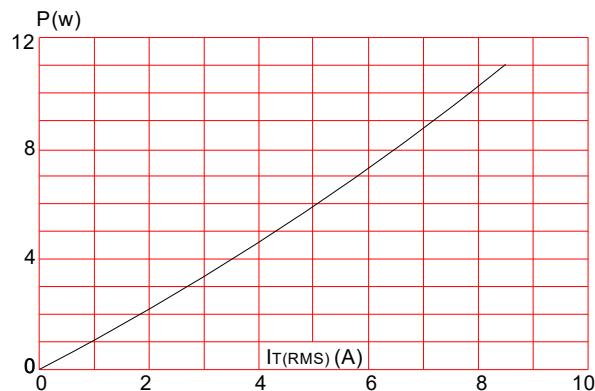


FIG.3: Surge peak on-state current versus number of cycles

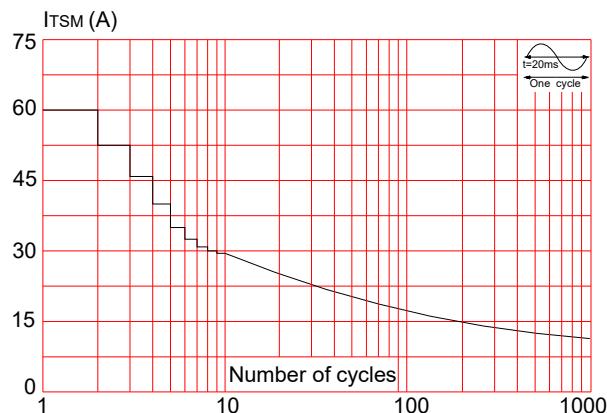


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II - III: $dl/dt < 50\text{A}/\mu\text{s}$; IV: $dl/dt < 10\text{A}/\mu\text{s}$)

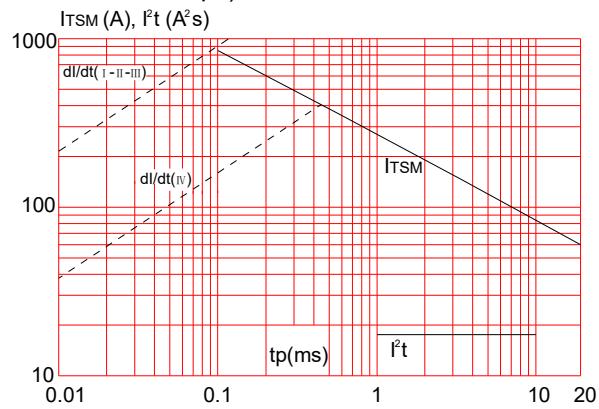


FIG.2: RMS on-state current versus case temperature

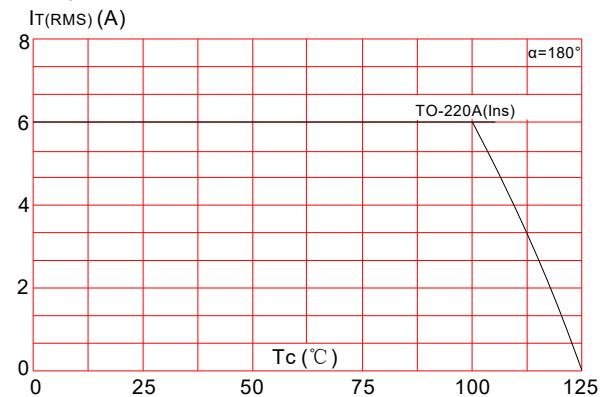


FIG.4: On-state characteristics (maximum values)

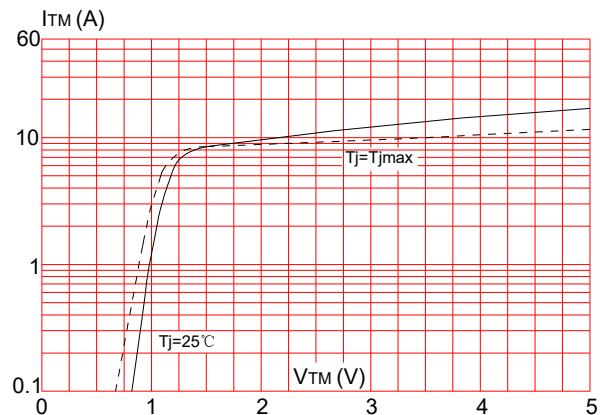


FIG.6: Relative variations of gate trigger current versus junction temperature

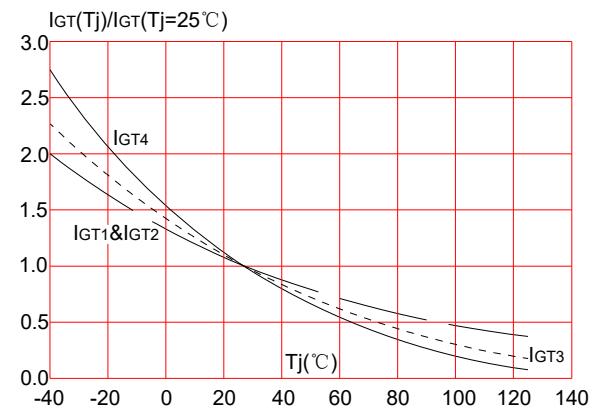


FIG.7: Relative variations of holding current versus junction temperature

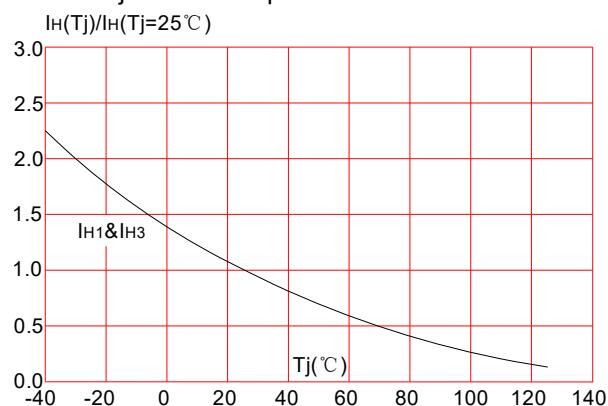
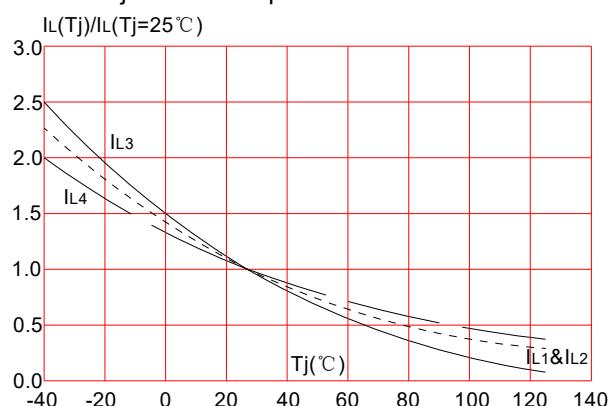


FIG.8: Relative variations of latching current versus junction temperature



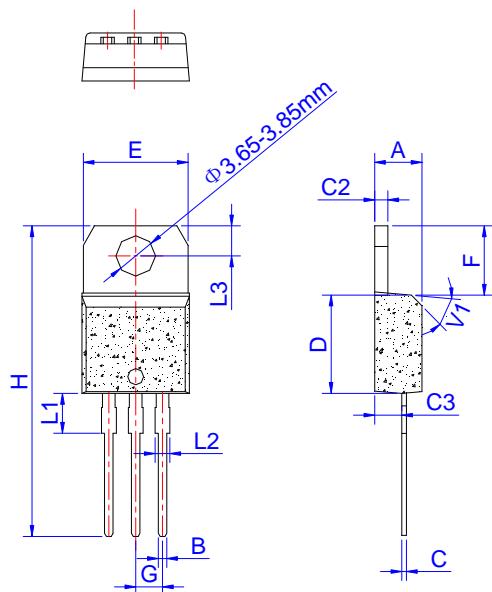
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JST06A-600BW	600	50	TO-220A(Ins)	50	Tube

Document Revision History

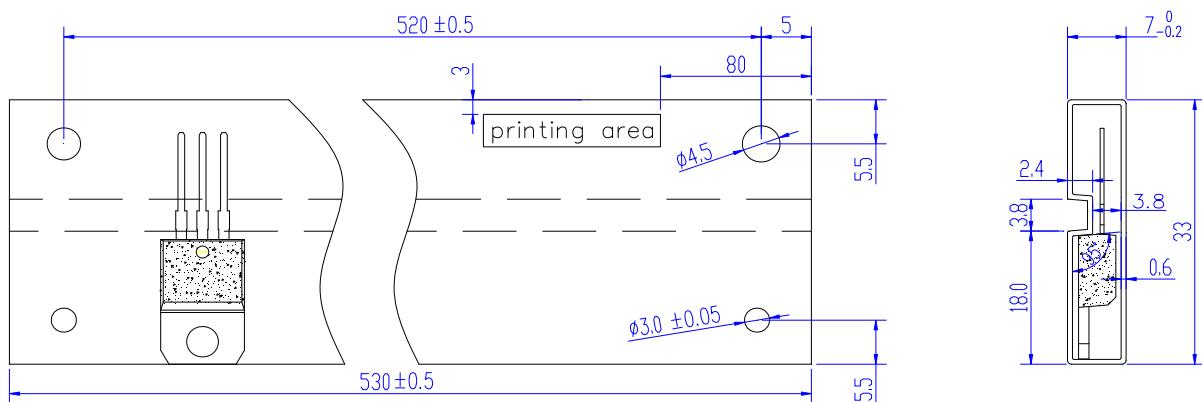
Date	Revision	Changes
Mar 22, 2022	1	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	TUBE	50	1,000	5,000



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